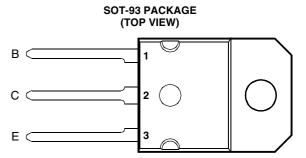
BOURNS®

- Designed for Complementary Use with the BD249 Series
- 125 W at 25°C Case Temperature
- 25 A Continuous Collector Current
- 40 A Peak Collector Current
- Customer-Specified Selections Available



Pin 2 is in electrical contact with the mounting base.

MDTRAAA

1

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING			VALUE	UNIT
	BD250		-55	
Collector emitter voltage (P. = 100.0)	BD250A	V	-70	V
Collector-emitter voltage ($R_{BE} = 100 \Omega$)	BD250B	V _{CER}	-90	v
	BD250C		-115	
	BD250		-45	
Collector-emitter voltage (I _C = -30 mA)	BD250A	V	-60	V
	BD250B	V _{CEO}	-80	v
	BD250C		-100	
Emitter-base voltage			-5	V
Continuous collector current			-25	Α
Peak collector current (see Note 1)			-40	Α
Continuous base current			-5	Α
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)			125	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)			3	W
Unclamped inductive load energy (see Note 4)			90	mJ
Operating junction temperature range			-65 to +150	°C
Storage temperature range			-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds			250	°C

NOTES: 1. This value applies for $t_p \le 0.3$ ms, duty cycle $\le 10\%$.

- 2. Derate linearly to 150° C case temperature at the rate of 1 W/°C.
- 3. Derate linearly to 150°C free air temperature at the rate of 24 mW/°C.
- 4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)}$ = -0.4 A, R_{BE} = 100 Ω , $V_{BE(off)}$ = 0, R_S = 0.1 Ω , V_{CC} = -20 V.



electrical characteristics at 25°C case temperature

PARAMETER			TEST CONDITIO	DNS	MIN	TYP	P MAX	UNIT	
	Collector-emitter			BD250 BD250A	-45 -60				
V _{(BR)CEO}	breakdown voltage	$I_C = -30 \text{ mA}$	$I_B = 0$	BD250B	-80			V	
		(see Note 5)	BD250C	-100					
		V _{CE} = -55 V	$V_{BE} = 0$	BD250			-0.7		
1	Collector-emitter	$V_{CE} = -70 \text{ V}$	$V_{BE} = 0$	BD250A			-0.7	mA	
ICES	cut-off current	$V_{CE} = -90 V$	$V_{BE} = 0$	BD250B			-0.7	ША	
		V _{CE} = -115 V	$V_{BE} = 0$	BD250C			-0.7		
1	Collector cut-off	$V_{CE} = -30 \text{ V}$	I _B = 0	BD250/250A			-1	mA	
ICEO	current	$V_{CE} = -60 \text{ V}$	$I_B = 0$	BD250B/250C			-1	ША	
I _{EBO}	Emitter cut-off current	V _{EB} = -5 V	I _C = 0				-1	mA	
	Forward current transfer ratio	V _{CE} = -4 V	I _C = -1.5 A		25				
h _{FE}		transfer ratio $V_{CE} = -4$	$V_{CE} = -4 V$	$I_{C} = -15 A$	(see Notes 5 and 6)	10			
		$V_{CE} = -4 V$	-		5				
V _{CE(sat)}	Collector-emitter	I _B = -1.5 A	$I_{\rm C} = -15 {\rm A}$	(see Notes 5 and 6)			-1.8	V	
* CE(sat)	saturation voltage	I _B = -5 A	-				-4	•	
V _{BE}	Base-emitter	V _{CE} = -4 V	I _C = -15 A	(see Notes 5 and 6)			-2	٧	
*BE	voltage	$V_{CE} = -4 V$	$I_C = -25 A$				-4	•	
h _{fe}	Small signal forward current transfer ratio	V _{CE} = -10 V	I _C = -1A	f = 1 kHz	25				
h _{fe}	Small signal forward current transfer ratio	V _{CE} = -10 V	I _C = -1 A	f = 1 MHz	3				

NOTES: 5. These parameters must be measured using pulse techniques, t_p = 300 μ s, duty cycle \leq 2%.

thermal characteristics

	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			1	°C/W
$R_{\theta,JA}$	Junction to free air thermal resistance			42	°C/W

resistive-load-switching characteristics at 25°C case temperature

	PARAMETER	TEST CONDITIONS †		MIN	TYP	MAX	UNIT	
t _{on}	Turn-on time	I _C = -5 A	$I_{B(on)} = -0.5 A$	$I_{B(off)} = 0.5 A$		0.2		μs
t _{off}	Turn-off time	$V_{BF(off)} = 5 \text{ V}$	$R_1 = 5 \Omega$	$t_{\rm p} = 20 \ \mu s, \ dc \le 2\%$		0.4		μs

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

^{6.} These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN VS COLLECTOR CURRENT TCS636AD TCS636AD

Figure 1.

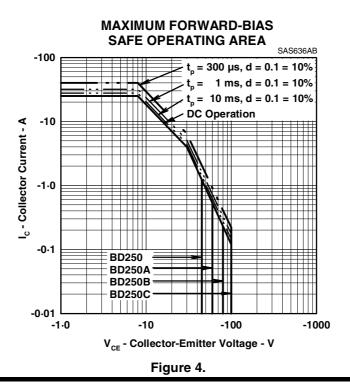
COLLECTOR-EMITTER SATURATION VOLTAGE vs **BASE CURRENT** TCS636AB -10 V_{CE(sat)} - Collector-Emitter Saturation Voltage - V -1.0 -0.1 300 mA -1 A -3 A -0.01 -0.01 -0.001 -0.1 -1.0 -10 -100 I_B - Base Current - A

Figure 2.

BASE-EMITTER VOLTAGE COLLECTOR CURRENT TCS636AC -1.8 $V_{CE} = -4 V$ $T_{\rm C} = 25^{\circ}{\rm C}$ -1.6 V_{BE} - Base-Emitter Voltage - V -1.4 -1.2 -1.0 -0.8 -0.6 -0.1 -10 -100 I_c - Collector Current - A Figure 3.

PRODUCT INFORMATION

MAXIMUM SAFE OPERATING REGIONS



THERMAL INFORMATION

MAXIMUM POWER DISSIPATION

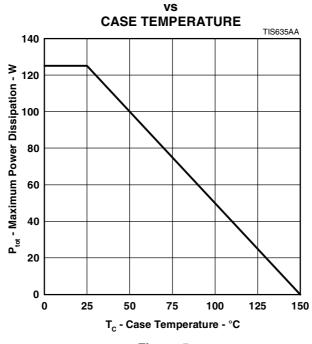


Figure 5.